## **REMARKS**

This paper is in response to the Notice of Non-Compliant Amendment dated June 22, 2005. The Notice, and in the telephonic conference conducted with the Examiner on July 5, 2005, indicates that the Amendment, filed on April 11, 2005, does not show all of the changes to claim 8. The Notice sets a time limit, without penalty, to resubmit the amendments to the claims by July 22, 2005. Accordingly, a complete listing of the claims is now being presented, including the underlined change to claim 8. Specifically, the language added to claim 8, "other gases," has now been properly underlined.

Consequently, claim 8 now recites a method of fabricating a semiconductor device comprising, *inter alia*, "depositing an oxygen-deficient dielectric film . . . subjecting the dielectric film to a densifying treatment . . . subjecting said stabilized dielectric film to a wet oxidation with steam process, said steam being carried to a rapid thermal process chamber, wherein said rapid thermal process chamber is kept at a temperature of at least about 450°C, wherein the ratio of steam to other gases . . . is in the range of about 0.1 to about 0.5, and wherein the pressure . . . is held at about atmospheric pressure; and subjecting the dielectric film to a second heat treatment," as recited in claim 8.

As indicated in the Amendment, filed on April 11, 2005, steam is carried to the rapid thermal process chamber. As a result, the rapid thermal process chamber can be held at about atmospheric pressure. Claim 8 does not recite that steam is formed within the rapid thermal process chamber. Thus, when steam enters the rapid thermal process chamber, the ratio of steam, to any other gases present in the rapid thermal process chamber, is in the range of about 0.1 to about 0.5. Moreover, the dielectric film undergoes two heat treatments. The first heat treatment is a densifying treatment that stabilizes the dielectric film before the wet oxidation with steam process. The second

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heat treatment occurs after the wet oxidation with steam process is completed. The prior art of record does not teach or suggest these claimed features.

In view of the above and the Remarks presented in the April 11, 2005 Amendment, each of the presently pending claims in this application is believed to be in immediate condition for allowance. Accordingly, the Examiner is respectfully requested to review and pass this application to issue.

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Respectfully submitted,

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